

# **Silicon Power Transistors**

The MJ21193 and MJ21194 utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

- Total Harmonic Distortion Characterized
- High DC Current Gain -

 $h_{FE} = 25 \text{ Min } @ I_C = 8 \text{ Adc}$ 

- Excellent Gain Linearity
- High SOA: 2.5 A, 80 V, 1 Second

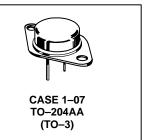
# **MAXIMUM RATINGS**

Rating	Sym- bol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	250	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	400	Vdc
Emitter–Base Voltage	V <sub>EBO</sub>	5	Vdc
Collector–Emitter Voltage – 1.5 V	$V_{CEX}$	400	Vdc
Collector Current — Continuous Peak (1)	I <sub>C</sub>	16 30	Adc
Base Current — Continuous	Ι <sub>Β</sub>	5	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C	P <sub>D</sub>	250 1.43	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

# **PNP** MJ21193\*

\*ON Semiconductor Preferred Device

16 AMPERE **COMPLEMENTARY SILICON POWER TRANSISTORS 250 VOLTS 250 WATTS** 



# THERMAL CHARACTERISTICS

Characteristic		Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typical	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage $(I_C = 100 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	250	_	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 200 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	_	_	100	μAdc

<sup>(1)</sup> Pulse Test: Pulse Width = 5 μs, Duty Cycle ≤10%. (continued)

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typical	Max	Unit
OFF CHARACTERISTICS						•
Emitter Cutoff Current $(V_{CE} = 5 \text{ Vdc}, I_C = 0)$		I <sub>EBO</sub>	_	_	100	μAdc
Collector Cutoff Current (V <sub>CE</sub> = 250 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc)	I <sub>CEX</sub>	_	_	100	μAdc	
SECOND BREAKDOWN				•		•
Second Breakdown Collector Current with Base For Biased (V <sub>CE</sub> = 50 Vdc, t = 1 s (non–repetitive) (V <sub>CE</sub> = 80 Vdc, t = 1 s (non–repetitive)	I <sub>S/b</sub>	5 2.5	=		Adc	
ON CHARACTERISTICS						
DC Current Gain ( $I_C = 8$ Adc, $V_{CE} = 5$ Vdc) ( $I_C = 16$ Adc, $I_B = 5$ Adc)		h <sub>FE</sub>	25 8		75	
Base–Emitter On Voltage (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 5 Vdc)		V <sub>BE(on)</sub>	_	_	2.2	Vdc
Collector–Emitter Saturation Voltage ( $I_C = 8$ Adc, $I_B = 0.8$ Adc) ( $I_C = 16$ Adc, $I_B = 3.2$ Adc)		V <sub>CE(sat)</sub>		_	1.4 4	Vdc
DYNAMIC CHARACTERISTICS						
Total Harmonic Distortion at the Output V <sub>RMS</sub> = 28.3 V, f = 1 kHz, P <sub>LOAD</sub> = 100 W <sub>RMS</sub>	h <sub>FE</sub> unmatch	T <sub>HD</sub>	_	0.8	_	%
ed (Matched pair h <sub>FE</sub> = 50 @ 5 A/5 V)	h <sub>FE</sub> matched		_	0.08	_	
Current Gain Bandwidth Product (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1 MHz)		f <sub>T</sub>	4	_	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)		C <sub>ob</sub>	_	_	500	pF

<sup>(1)</sup> Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2%

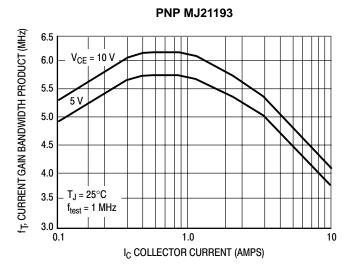


Figure 1. Typical Current Gain Bandwidth Product

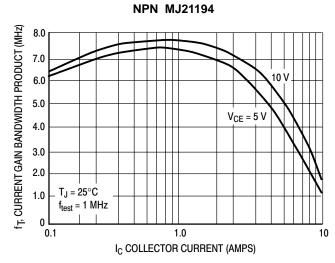


Figure 2. Typical Current Gain Bandwidth Product

# TYPICAL CHARACTERISTICS

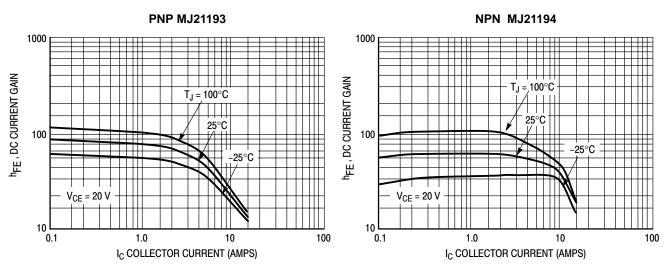


Figure 3. DC Current Gain, V<sub>CE</sub> = 20 V

Figure 4. DC Current Gain, V<sub>CE</sub> = 20 V

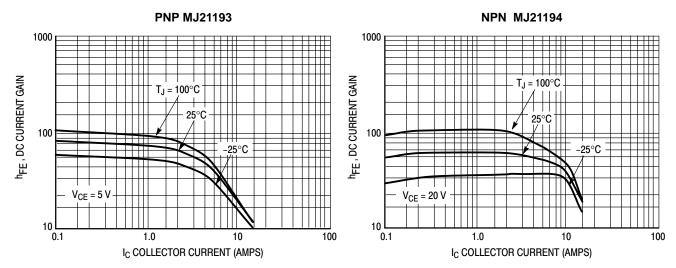


Figure 5. DC Current Gain,  $V_{CE} = 5 \text{ V}$ 

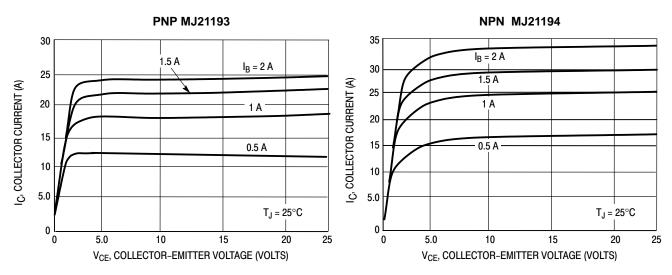


Figure 7. Typical Output Characteristics

**Figure 8. Typical Output Characteristics** 

Figure 6. DC Current Gain,  $V_{CE} = 5 \text{ V}$ 

#### TYPICAL CHARACTERISTICS

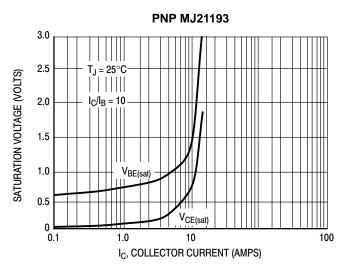


Figure 9. Typical Saturation Voltages

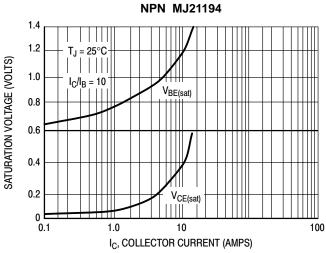


Figure 10. Typical Saturation Voltages

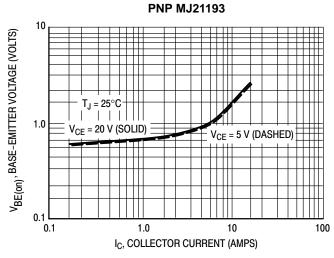


Figure 11. Typical Base-Emitter Voltage

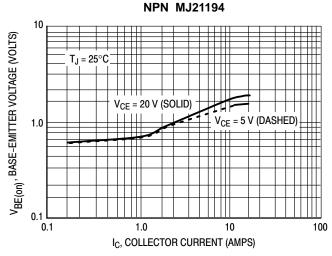


Figure 12. Typical Base-Emitter Voltage

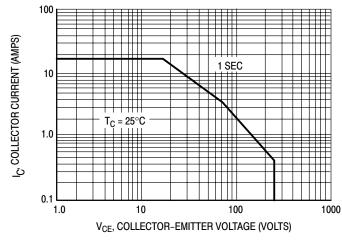


Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on  $T_{J(pk)} = 200^{\circ}\text{C}$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

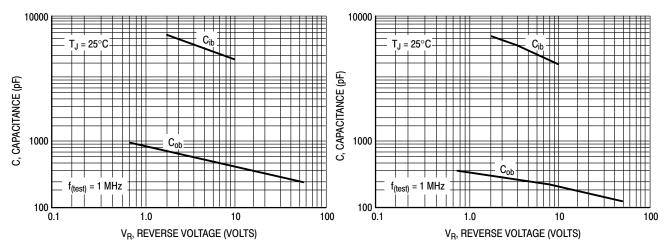
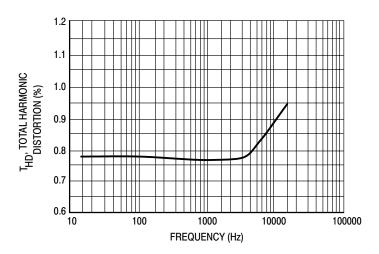


Figure 14. MJ21193 Typical Capacitance

Figure 15. MJ21194 Typical Capacitance



**Figure 16. Typical Total Harmonic Distortion** 

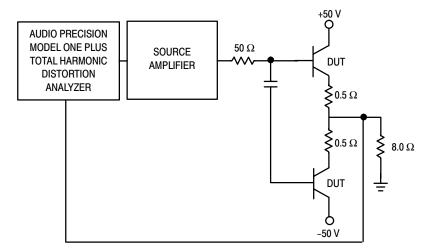
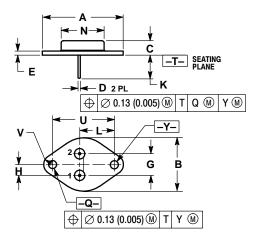


Figure 17. Total Harmonic Distortion Test Circuit

# **PACKAGE DIMENSIONS**

**CASE 1-07** TO-204AA (TO-3) ISSUE Z



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37	REF	
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
Е	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215	0.215 BSC		BSC	
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89	BSC	
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
5	1.187 BSC		30.15 BSC		
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR



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